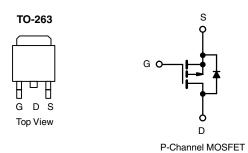


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Vishay Siliconix

# Automotive P-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	- 60				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.015				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.022				
I <sub>D</sub> (A)	- 50				
Configuration	Single				



#### **FEATURES**

- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- 100 % R<sub>q</sub> and UIS Tested
- AEC-Q101 Qualified<sup>d</sup>
- Material categorization:
   For definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>





ORDERING INFORMATION	
Package	TO-263
Lead (Pb)-free and Halogen-free	SQM50P06-15L-GE3

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		$V_{DS}$	- 60	V	
Gate-Source Voltage	$V_{GS}$	± 20	V		
Cantinua Dunia Commant	T <sub>C</sub> = 25 °C <sup>a</sup>	1	- 50		
Continuous Drain Current	T <sub>C</sub> = 125 °C	l <sub>D</sub>	- 41		
Continuous Source Current (Diode Conduc	I <sub>S</sub>	- 50	Α		
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	- 200			
Single Pulse Avalanche Current	1 04	I <sub>AS</sub>	- 50		
Single Pulse Avalanche Energy	L = 0.1 mH	E <sub>AS</sub>	125	mJ	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	1	150	14/	
	T <sub>C</sub> = 125 °C	$P_{D}$	50	W	
Operating Junction and Storage Temperatu	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C		

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient	PCB Mount <sup>c</sup>	$R_{thJA}$	40	°C/W		
Junction-to-Case (Drain)		$R_{thJC}$	1	C/VV		

### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT		
Static								
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0, I <sub>D</sub> = - 250 μA		- 60	-	-	V	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	V <sub>GS</sub> , I <sub>D</sub> = - 250 μA	- 1.5	-	- 2.5	V	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 60 V	-	-	- 1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 60 V, T <sub>J</sub> = 125 °C	-	-	- 50	μΑ	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 60 V, T <sub>J</sub> = 175 °C	-	-	- 150	1	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = - 10 V	$V_{DS} \le -5 V$	- 50	-	-	Α	
		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 17 A	-	0.013	0.015	Ω	
Dunin Course On Otata Basistanas		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 17 A, T <sub>J</sub> = 125 °C	-	-	0.025		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 17 A, T <sub>J</sub> = 175 °C	-	-	0.030		
		V <sub>GS</sub> = - 4.5 V	I <sub>D</sub> = - 14 A	-	0.018	0.022		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 17 A		-	46	-	S	
Dynamic <sup>b</sup>								
Input Capacitance	C <sub>iss</sub>				4896	6120		
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = - 25 V, f = 1 MHz	-	480	600	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	348	435		
Total Gate Charge <sup>c</sup>	Qg			-	103	155		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = - 10 V	$V_{DS} = -30 \text{ V}, I_{D} = -50 \text{ A}$	-	16.6	-	nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	26.6	-		
Gate Resistance	R <sub>g</sub>		f = 1 MHz		2.6	3.9	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	13	20		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = -30 \text{ V}, R_L = 0.6 \Omega$ $I_D \cong -50 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 1 \Omega$		-	10	15	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	60	90		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	16	24		
Source-Drain Diode Ratings and Char	acteristics <sup>b</sup>							
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	- 200	Α	
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> =	I <sub>F</sub> = - 30 A, V <sub>GS</sub> = 0		- 0.9	- 1.5	V	

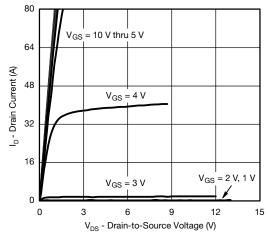
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

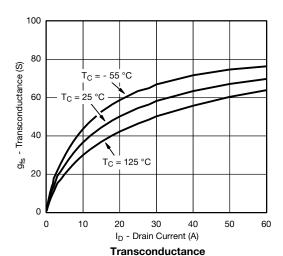
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



# TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)







7000
6000
Coss
1000
Coss

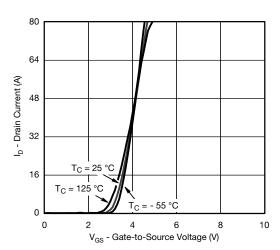
V<sub>DS</sub> - Drain-to-Source Voltage (V)

Capacitance

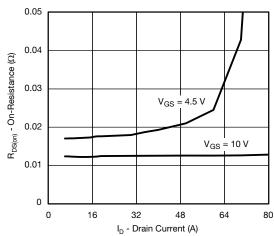
8000

0

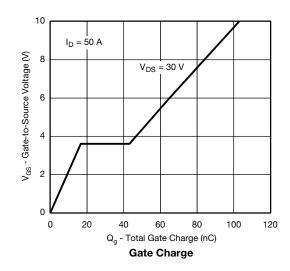
10



**Transfer Characteristics** 

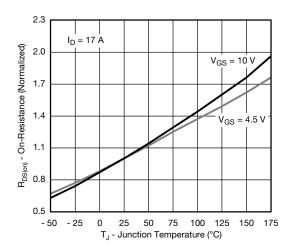


On-Resistance vs. Drain Current

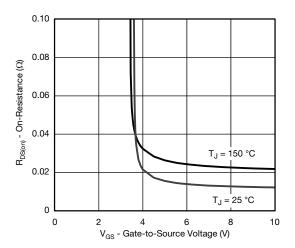




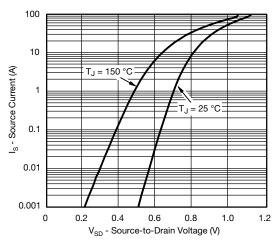
# TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



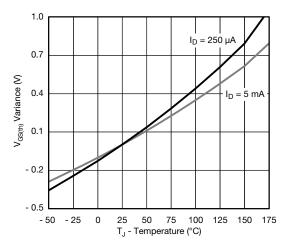
#### On-Resistance vs. Junction Temperature



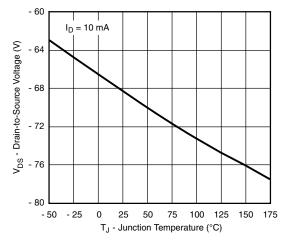
On-Resistance vs. Gate-to-Source Voltage



**Source Drain Diode Forward Voltage** 



**Threshold Voltage** 

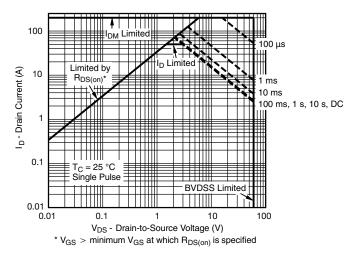


**Drain Source Breakdown vs. Junction Temperature** 

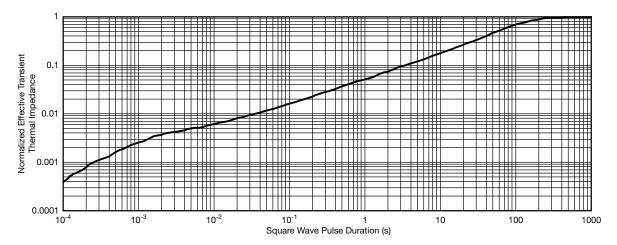
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# **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



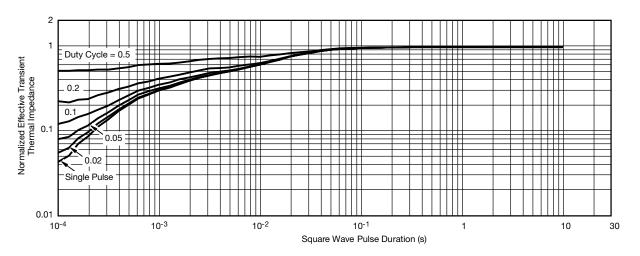
#### Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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# THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction to Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg267001">www.vishay.com/ppg267001</a>.



# TO-263 (D<sup>2</sup>PAK): 3-LEAD









DETAIL A (ROTATED 90°)



⋝:	,	 	b— b1–		ļ	ļ
2:	П				5	ပ
	SE	СТ	ION	ΙΔ.	- 1 - Δ	Ŧ

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. \*: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6 This feature is for thick lead.

		INCHES		MILLIMETERS		
	DIM.	MIN.	MAX.	MIN.	MAX.	
Α		0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457	
	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.042	0.965	1.067	
D3		0.045	0.055	1.143	1.397	
D4		0.044	0.052	1.118	1.321	
	Е	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	-	
	E2	0.355	0.375	9.017	9.525	
	E3	0.072	0.078	1.829	1.981	
	е	0.100	BSC	2.54 BSC		
	K	0.045	0.055	1.143	1.397	
	L	0.575	0.625	14.605	15.875	
L1		0.090	0.110	2.286	2.794	
L2		0.040	0.055	1.016	1.397	
L3		0.050	0.070	1.270	1.778	
	L4	0.010 BSC		0.254 BSC		
	М	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13						

DWG: 5843





# RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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